M/A-COM

3 Volt Voltage Variable Absorptive Attenuator 40 dB, 0.5 - 2 GHz



Features

- Single Positive Voltage Control 0 to +3 Volts
- 40 dB Attenuation Range at 0.9 GHz
- ± 2 dB Linearity from BSL
- Low DC Power Consumption
- Low Cost SOIC-8 Plastic Package
- Tape and Reel Packaging Available

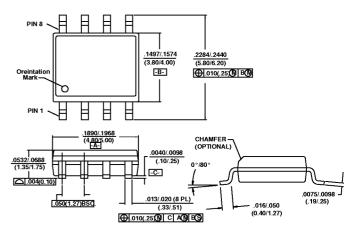
Description

M/A-COM's AT-113 is a GaAs MMIC voltage variable absorptive attenuator in a low cost SOIC 8-lead surface mount plastic package. The AT-113 is ideally suited for use where linear attenuation fine tuning and very low power consumption are required.

Typical applications include radio, cellular, GPS equipment and automatic gain/level control circuits.

The AT-113 is fabricated with a monolithic GaAs MMIC using a mature 1-micron process. The process features full chip passivation for increased performance and reliability.

SOIC-81



Dimensions are in inches/mm.

Ordering Information

Part Number	Package	
AT-113	SOIC-8 Lead Plastic	
AT-113TR	Forward Tape and Reel ¹	

1. If specific reel size is required, consult factory for part number assignment.

Electrical Specifications: T_A = +25°C

Parameter	Test Conditions	Units	Min.	Тур.	Max.
Insertion Loss	0.5 - 1.0 GHz	dB		2.7	3.0
	1.0 - 2.0 GHz	dB		3.0	3.5
Attenuation	0.5 - 1.0 GHz	dB	40		
	1.0 - 2.0 GHz	dB	35		
Insertion Loss Flatness (Peak-to-Peak)	0.5 - 1.0 GHz	dB		±0.5	±0.8
	1.0 - 2.0 GHz	dB		±1.2	±1.5
VSWR				2:1	
T_{rise}, T_{fall}	10% to 90% RF, 90% to 10% RF	μS		10	
T _{on} , T _{off}	50% Control to 90% RF, Control to 10% RF	μS		12	
Transients	In-band	mV		10	

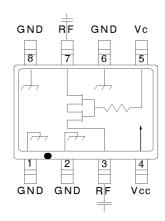
All measurements at 1 GHz in a 50Ω system unless otherwise specified. The RF ports must be blocked out side of the package from ground or any other voltage.

Absolute Maximum Ratings¹

Parameter	Absolute Maximum			
Maximum Input Power	+21 dBm			
Supply Voltage V _{CC}	-1V, +8V			
Control Voltage V _C	-1V, V _{cc} +0.5V			
Operating Temperature	-40°C to +85°C			
Storage Temperature	-65°C to +150°C			

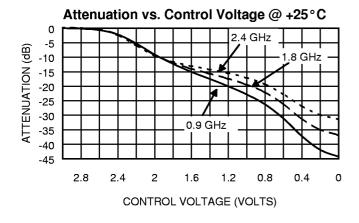
 Exceeding any one or a combination of these limits may cause permanent damage.

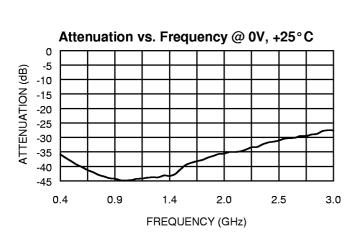
Functional Schematic^{1, 2, 3}

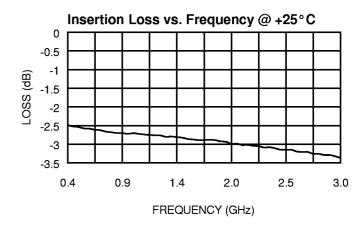


- 1. $V_{CC} = -3 V_{DC} @ 50 \mu A max.$
- 2. $V_C = 0 V_{DC}$ to +3 V_{DC} @ 50 μ A max.
- 3. External DC blocking capacitors are required on all RF ports.
- 4. 39pF used for data measurements.

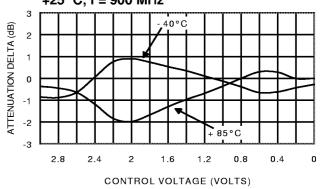
Typical Performance Curves







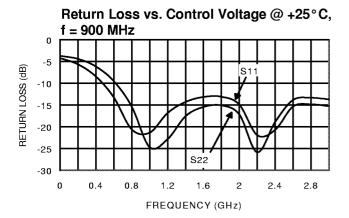


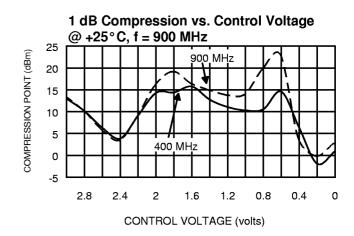


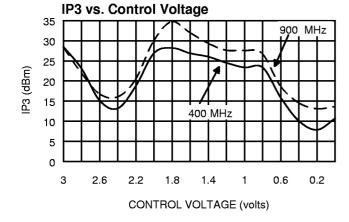
V2.00

Connecting
HIGHER
level.**

Typical Performance Curves (Cont'd)







Connecting at a HGHER level."